



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Robert Bertram Ogle, Jr.; Arvind Halliyal
Assignee: Advanced Micro Devices, Inc.
Title: Process For Treating ONO Dielectric Film Of A Floating Gate Memory Cell
Serial No.: 09/927,134 Filing Date: August 10, 2001
Examiner: Howard Weiss Group Art Unit: 2814
Docket No.: M-7525 US Client Ref.: D897

7/Amend A
8/50/02
C. Paris

San Jose, California
August 5, 2002

COMMISSIONER FOR PATENTS
Washington, D. C. 20231

RESPONSE TO OFFICE ACTION

Dear Sir:

This is a response to the April 10, 2002 Office Action, which has a statutorily shortened period that ends on July 10, 2002. Please enter the following amendments before taking action on the merits of the above-referenced application. A one-month extension of time accompanies this Response, allowing the Applicants until August 10, 2002 to respond.

In the Claims

The following is a clean version of the entire set of pending Claims 1-25. In accordance with 37 CFR § 1.121(c)(1)(ii), an attachment provides marked up versions of the amended claims containing the newly introduced changes. The attached page is captioned

"Version with markings to show changes made."

Claims 2 and 9-11 are amended and Claims 1 and 20-25 are cancelled.

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